

# **APPLICATION NOTE**

# DESIGNING A HIGH POWER FACTOR SWITCHING PREREGULATOR WITH THE L4981 CONTINUOUS MODE

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#### INTRODUCTION

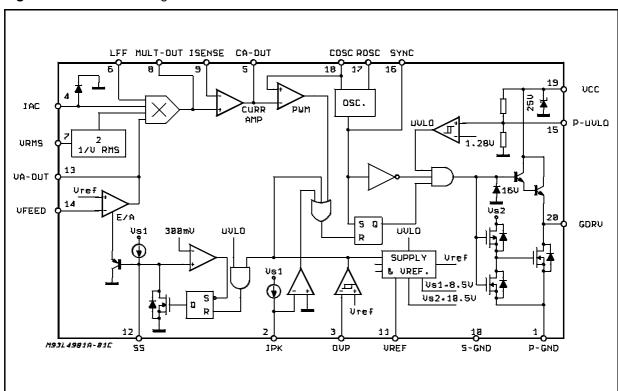
Conventional AC-DC converters usually employ a full wave rectifier bridge with a simple capacitor filter to draw power from the AC line. This "bulk" capacitor must be big enough to supply the total power during most of each half-cycle, while instantaneous line voltage is below the DC rectified voltage. Consequentely, the line current waveform is a narrow pulse, and the power factor is poor (0.5-0.6) due to the high harmonic distortion of the current waveform.

If a high power factor switching preregulator is interposed between the input rectifier bridge and the bulk filter capacitor, the power factor will be improved (up to 0.99). Increasing in addition, the RMS current capability from the mains, reducing the bulk capacitor peak current and the harmonic disturbances.

Switching at a frequency much higher than the line's one, the preregulator draws a sinusoidal input current, in phase with the input line voltage.

There are several way that this can be accomplished. When the output voltage is higher than the input voltage (Vo > Vin), BOOST topology and continuos inductor current control mode are well suited to produce a good quality input sine current waveform. The input di/dt is low because the inductor is located between the bridge and the switch. This minimizes line noise and the line spikes will be absorbed by the inductor.

Figure 1: L4981 Block Diagram



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#### THE L4981 PFC CONTROLLER IC

The L4981 integrated circuit is a continous mode average current controller with several specific functions for active power factor correction. It can operate in high quality, medium/high power conversion range and provides all the necessary features to achieve a very high power factor, up to 0.99. Thanks to the BCD technology used, operative switching frequency higher than 200kHz can be used.

The L4981 can be used in systems with universal input mains voltage without any line switch.

This new PFC offers the alternative of synchronization working at fixed frequency (L4981A), or working in modulated frequency (L4981B) to optimize the size of the input filter. Both devices control the conversion in average current mode PWM to maintain a sinusoidal line current without slope compensation.

#### **MAIN FEATURES:**

- Switching frequency higher than 200 kHz.
- Under Voltage Lockout with hysteresis and programmable turn-on threshold.
- Overvoltage and Overcurrent Protection.
- Precise (2%) on chip Reference externally available.
- Input/Output Synchronization (only for L4981A).
- Feed Forward Line and Load regulation.
- Universal input mains.
- Average current mode PWM.
- High Output Current totem pole driver.
- Low Start-up supply current.
- Soft Start.

## Figure 2.

## P.F.C. BOOST TOPOLOGY OPERATION

The operation of the P.F.C. boost converter (see fig. 2) can be summarized in the following description.

The A.C. line voltage is rectified by a diode bridge and the rectified voltage delivered to the boost converter. The boost converter section, using a PWM switching technique, boosts the rectified input voltage to a D.C. controlled output voltage ( $V_O$ ). The section consists of a boost inductor (L), a controlled power switch (Q), a boost diode (D), an output capacitor ( $C_O$ ) and, obviously, a control circuitry.

Referring to the time-variable mains voltage (sine waveform), the converter produces a boost inductor average current like the rectified input voltage, changing continuosly the duty-cycle of the active switch (Q).

The boosted D.C. voltage is controlled to a programmed value, higher than the maximum input instantaneous voltage (V<sub>Ipk</sub>).

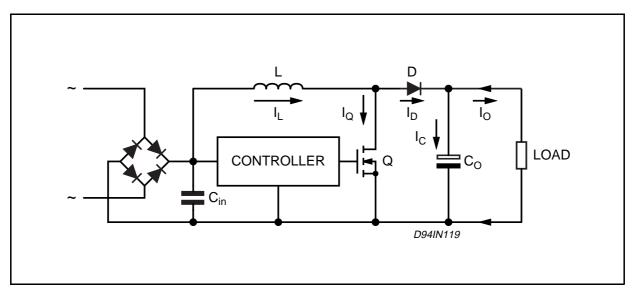
Referring to the main currents shown in fig.2 schematic, the simplified formulae are (assuming: power efficiency = 1; output ripple voltage = 0; high frequency inductor ripple current = 0):

1) Peak inductor (L), switch (Q) and diode (D) currents

$$I_{Lpk} = I_{Qpk} = I_{Dpk} = 2 \cdot \frac{P_O}{V_{lpk}}$$

2) RMS inductor current

$$I_{Lrms} = \sqrt{2} \cdot \frac{P_O}{V_{lnk}}$$



3) RMS switch current

$$I_{Qrms} = \frac{P_O}{V_{lpk}} \cdot \sqrt{2 - \frac{16 \cdot V_{lpk}}{3 \cdot \pi \cdot V_O}}$$

4) Average diode current

$$I_{Davg} = I_{O}$$

5) RMS diode current

$$I_{Drms} = \frac{P_O}{V_{lpk}} \cdot \sqrt{\frac{16 \cdot V_{lpk}}{3 \cdot \pi \cdot V_O}}$$

6) Total RMS capacitor (Co) current

$$I_C = I_O \sqrt{\frac{16 \cdot V_O}{3 \cdot \pi \cdot V_{lok}} - 1}$$

7) RMS twice line frequency capacitor current

$$I_{C (2f) rms} = \frac{I_O}{\sqrt{2}}$$

8) RMS high frequency capacitor current

Ic (hf) rms = Io 
$$\sqrt{\frac{16 \cdot V_O}{3 \cdot \pi \cdot V_{lpk}}} - 1.5$$

The figure 3 shows the above mentioned quantities, normalized to the D.C. output current ( $I_O$ ), plotted versus  $V_{Ipk}$  /  $V_O$  ratio. Moreover, the  $I_{Lpk} \cdot I_{Lrms}$  normalized to  $I_O^2$  value, related to the inductor energy ( $I^2 \cdot L$ ), is plotted in the diagram (dotted line). This last plot gives an idea on the heavy increase of the inductor size operating with large input voltage range.

Obviously, in real application the efficiency is less than 100% ( $\eta < 1$ ). The output voltage ripple, related to the output capacitor (Co) is a parameter to be considered. The inductor high frequency current ripple ( $\Delta I_L$ ) is another parameter affected by the inductor value (L), the switching frequency ( $f_{sw}$ ) and the delivered power (Po).

Figure 3.

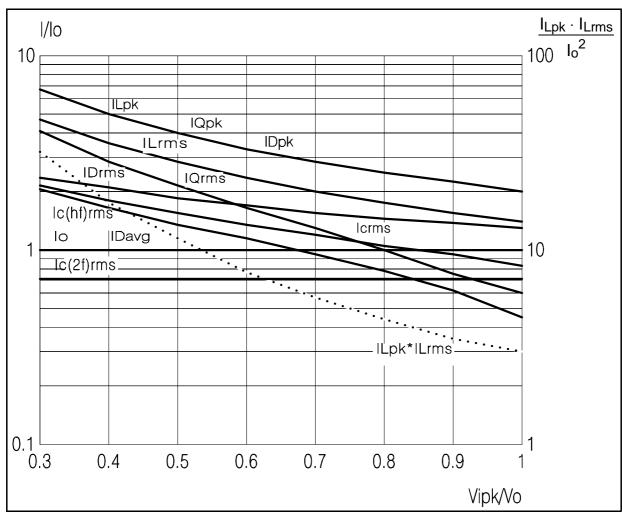
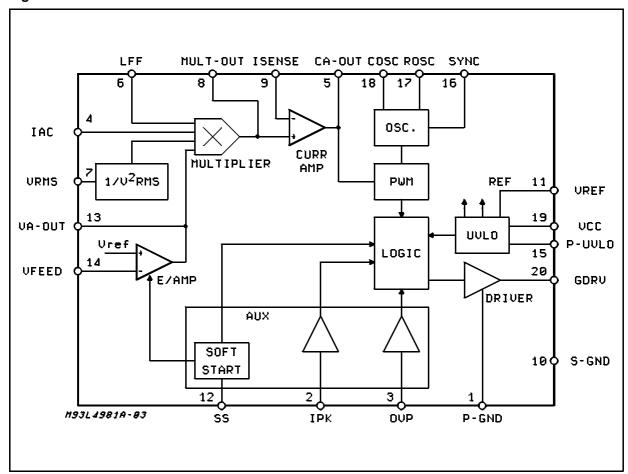


Figure 4.



#### CONTROLLER FUNCTION DESCRIPTION.

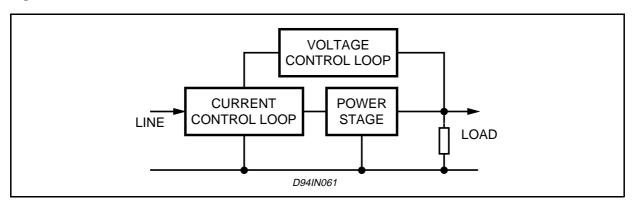
The L4981 I.C. controls the conversion process with a continuous mode average current method, using two control loops (current loop and voltage loop) see fig. 5. Moreover, several internal functions ensure high quality conversion performance.

A description of the internal blocks will be detailed in the design criteria section and pin description. However, referring to fig. 4, here below a brief description of the main functions is done:

## Multiplier block.

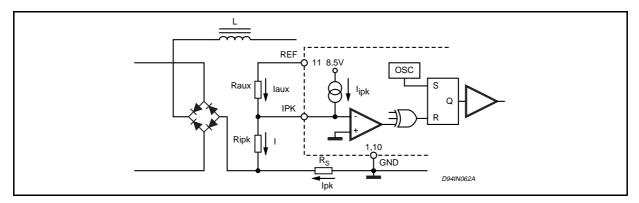
This block produces an output current (programming current) as a product result of four different input signals (see fig. 13 for details). The multiplier output current, through a resistor connected to the negative side of a sense resistor, determines the error signal to the current loop.

Figure 5.



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Figure 6.



## Operational amplifier blocks.

Two amplifiers allow loop control. The first one (E/A), feeds back the output voltage  $(V_O)$  and delivers its output to the multiplier block. The second (C/A), feeds back the line current and produces the reference for the PWM section.

#### PWM block.

This block, comparing the sawtooth produced by the oscillator, with the reference signal from the C/A output, modulates its output signal duty-cycle. Its output, by the logic and driver sections, allows the controlled switch (Q) to modulate the inductor current.

#### Logic block.

Controls the flow from the PWM and the output with the Auxiliary function signals and soft start.

## Driver block.

The driver supplies the gate current to turn on and off the power switch (Q). It delivers up to 1A peak current to allow high switching frequency applications.

## Aux functions.

The Auxiliary functions allow to avoid overstress on power components of the application.

# Power supply block.

This circuitry delivers the internal supply and references, recognizes the Undervoltage and Standby conditions to save consumption.

#### P.F.C. BOOST DESIGN CRITERIA

CONTROLLER DEVICE PIN DESCRIPTION AND BIASING CIRCUITRY.

**Pin 1.** P-GND (Power stage ground). This pin, on the pc-board, has to be connected close the external Mosfet source.

**Pin 2.** IPK (Overcurrent protection input). The current limitation is obtained with an internal comparator that holds down the output driver when the voltage at IPK input goes down to zero. In the L4981A, to preset the IPK input there is an internal current source ( $I_{ipk}$ ) of typically 85  $\mu$ A. The maximum peak current ( $I_{pk}$ ) can be programmed connecting (see fig. 6) a single resistor ( $R_{ipk}$ ) between this pin and the sense resistor ( $R_{ipk}$ ):

$$R_{ipk} = \frac{R_S \cdot I_{pk}}{I_{ipk}}$$

In the L4981B, to preset the IPK input, an auxiliary resistor ( $R_{aux}$ ), connected from the VREF pin to the IPK pin, is required. The maximum peak current ( $I_{pk}$ ) can be programmed choosing (see fig. 6) the resistances  $R_{aux}$  and  $R_{ipk}$ :

$$R_{ipk} = \frac{R_S \cdot I_{pk}}{I_{aux}}$$

Where: 
$$I_{aux} = \frac{V_{VREF}}{R_{aux}}$$

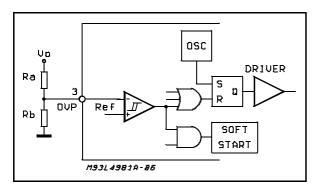
Note: If used with the L4981A, the auxiliary resistor avoids that the current source spread affects the precision of the protection simply getting an auxiliary current (I<sub>aux</sub>) much higher than I<sub>ipk</sub>.

**Pin 3.** OVP (Overvoltage protection input). A comparator with a precise 5.1V reference voltage and 250mV of hysteresis, detects the overvoltage condition and turns the controller in stand-by condition (with low power consumption) and discharges the soft start capacitor. This pin (see fig. 7) has to be externally connected with a resistive divider (Ra and Rb) to the D.C. output voltage. The divider ratio is defined by the relation:

$$\frac{Ra}{Rb} = \frac{V_O + \Delta V_{OUT}}{5.1V} - 1$$

where:  $\Delta V_{OUT}$  is the output overvoltage limit.

Figure 7.

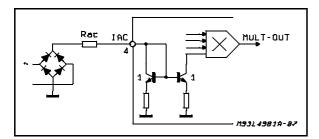


**Pin 4.** IAC (A.C. current input). This pin (see fig. 8) has to be connected through a resistor to the rectified line voltage to drive the multiplier with a current (I<sub>IAC</sub>) proportional to the instantaneous line voltage:

$$I_{IAC} = \frac{V_I}{R_{ac}}$$

The relation between the input alternate current (I<sub>IAC</sub>) and the output current (programming signal Imult) of the multiplier is described at MULT-OUT section (pin8).

Figure 8.



**Pin 5.** CA-OUT (Current amplifier output). The CA\_OUT deliveres its signal to the PWM comparator. An external network (see fig. 9) defines the suitable loop gain to process the multiplier output and the line current signals. To avoid oscillation problem (see fig. 10) the maximum inductor current downslope (V<sub>O</sub>/L) has to be lower than oscillator ramp-slope (V<sub>srp</sub> · f<sub>sw</sub>):

$$\frac{V_O}{I} \cdot R_s \cdot G_{ca} \leq V_{srp} \cdot f_{sw}$$

where:

 $V_{\text{srp}}$  is the oscillator ramp peak-peak voltage.  $G_{\text{ca}}$  is the current amplifier gain.  $f_{\text{sw}}$  is the switching frequency.

and rewritten as:

$$G_{ca} \leq \frac{V_{srp} \cdot f_{sw} \cdot L}{V_O \cdot R_s}$$

Figure 9.

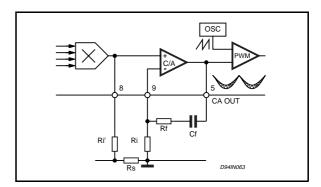
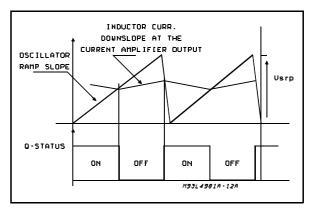


Figure 10.



defines the high frequency C/A gain (1 +  $\frac{R_f}{R_i}$ ):

$$\frac{R_f}{R_i} \leq \frac{V_{srp} \cdot f_{sw} \cdot L}{V_O \cdot R_s} - 1$$

To define the  $C_f$  value, it's useful to consider the current openloop gain, defined by the ratio between the voltage across  $R_s$  and the current amplifier output signal:

$$G_{avg} = \frac{v_{rs}}{v_{ca}}$$

Because, in worst condition is:

$$v_{rs} = \frac{R_s \cdot V_O}{s \cdot L}$$

and the total variation of  $v_{ca}$  (the reference signal for PWM) is  $V_{srp}$ :

$$G_{avg} = \frac{R_s \cdot V_O}{V_{sro} \cdot 2\pi \cdot f \cdot L}$$

Multiplying this  $G_{avg}$  by  $G_{ca}$  and solving for the crossover frequency (f =  $f_c$ ), follows:

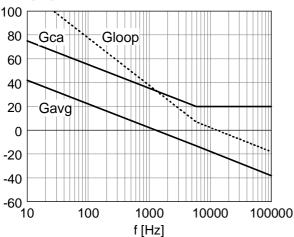
$$f_{\rm C} = \frac{f_{\rm SW}}{2 \, \pi}$$

To ensure a phase margin (higher than 45°), the zero frequency (fz) should be about fc/2, than:

$$f_z = \frac{f_{sw}}{4 \cdot \pi} = \frac{1}{2 \cdot \pi \; C_f \cdot R_f} \; \Rightarrow \; C_f = \frac{2}{R_f \cdot f_{sw}}$$

Figure 11.

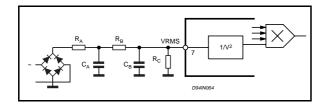




**Pin 6.** LFF (Load feed-forward input). This voltage input pin allows to modify the multiplier output current proportionally to the load in order to improve the response time versus load transient. The control is working with V<sub>LFF</sub> between 1.5V and 5.1V. If this function is not used, the LFF pin has to be connected to VREF pin. See also appendix A.

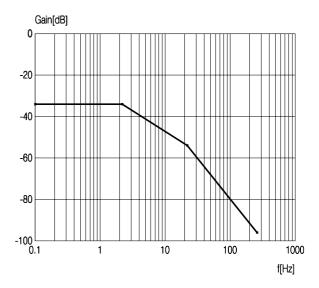
**Pin 7.** VRMS. Input to the divider  $(1/V^2_{RMS})$ , it is especially useful in universal mains applications to compensate the gain variation related to the input voltage change. It will be connected to an external network (see fig. 12a) giving a voltage level proportional to the mains  $V_{RMS}$ . The best control is reached using a VRMS voltage level in the range between 1.5V and 5.5V.

Figure 12a.



To avoid line current distorsion, the rectified mains ripple (2f) level has to be reduced. A two pole filter, with three resistors and two capacitors, setting the lowest pole at 2Hz and the highest one at 13Hz, is enough to get the useful voltage level reducing to -80dB the 100Hz gain.

Figure 12b.



The signal (pin 7), with the network in fig. 12a is:  $V_{RMS} = 85V (110V - 20\%) \quad VRM(7) = 1.6V$   $V_{RMS} = 260V (220V + 20\%) \quad VRM(7) = 5V$  Gain at 2f(100Hz) -80dB

**Pin 8.** MULT-OUT (Output of the multiplier). This pin deliveres the programming current (Imult) according to the relation:

$$I_{mult} = 0.37 \cdot I_{IAC} \cdot \frac{(V_{VA-OUT} - 1.28V) \cdot (0.8 \cdot V_{LFF} - 1.28V)}{VRMS^2}$$

where:  $V_{VA-OUT}$  = E/A output voltage range  $V_{LFF}$  = voltage input at pin 6  $V_{RMS}$  = voltage input at pin 7  $I_{IAC}$  = input current at pin 4

To optimize the multiplier biasing for each application, the relation between Imult and the other input signals to the multiplier are reported (see figures 13, 13a to 13h).

Figure 13.

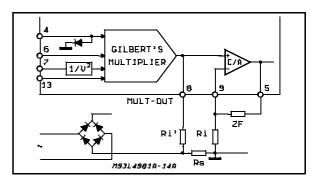


Figure 13a: MULTI-OUT vs.  $I_{AC}$  ( $V_{RMS} = 1.7V$ ;

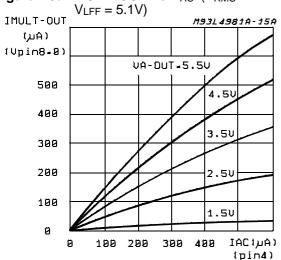


Figure 13b: MULTI-OUT vs. IAC ( $V_{RMS} = 2.2V$ ;

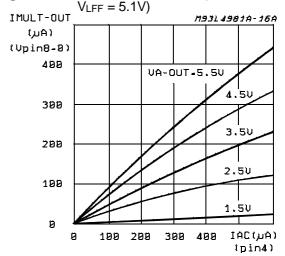


Figure 13c: MULTI-OUT vs. IAC ( $V_{RMS} = 4.4V$ ;

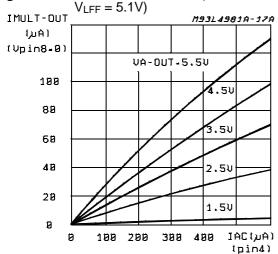


Figure 13d: MULTI-OUT vs. I<sub>AC</sub> ( $V_{RMS} = 5.3V$ ;

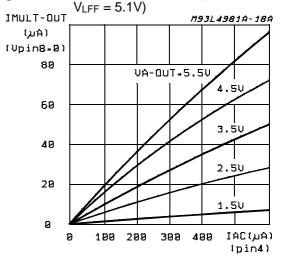


Figure 13e: MULTI-OUT vs. IAC ( $V_{RMS} = 1.7V$ ;

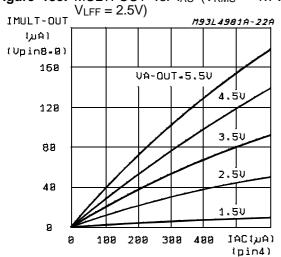


Figure 13f: MULTI-OUT vs.  $I_{AC}$  ( $V_{RMS} = 2.2V$ ;

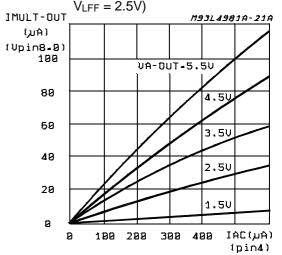


Figure 13g: MULTI-OUT vs. IAC ( $V_{RMS} = 4.4V$ ;  $V_{LFF} = 2.5V$ )

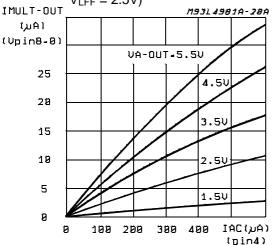
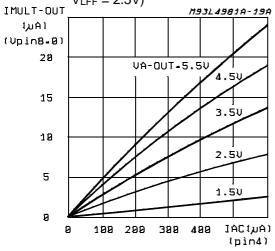


Figure 13h: MULTI-OUT vs. I<sub>AC</sub> ( $V_{RMS} = 5.3V$ ;  $V_{LFF} = 2.5V$ )



The pin has to be connected through a resistor (Ri') to the negative side of Rs (see fig. 9) to sum the ( $I_L \cdot R_S$ ) and the ( $I_{mult} \cdot Ri$ ') signals. The sum result is the error signal voltage to the current amplifier non inverting input.

$$Ri' \cdot I_{mult} = R_s \cdot I_L$$

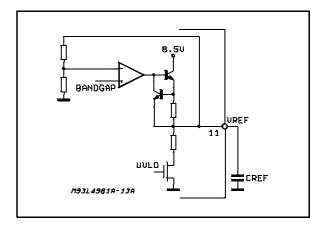
**Pin 9.** ISENSE (Current Amplifier inverting input). This pin, is externally connected to the external network described at CA-OUT (pin 5). To be noted that Ri and Ri' have the same value because of the high impedance feedback network.

**Pin 10.** SGND (Signal ground). It has to be connected, to the pc-board GND, close the filtering reference capacitor.

Pin 11. VREF (Voltage reference). An internal

bandgap circuitry, allows an accurate voltage reference. An external capacitor filter (from 100nF to some  $\mu F$ ) connected to the signal ground is recommanded (see fig. 14). This pin can deliver up to 10mA and can be used for external needs (e.g. enable for other circuits).

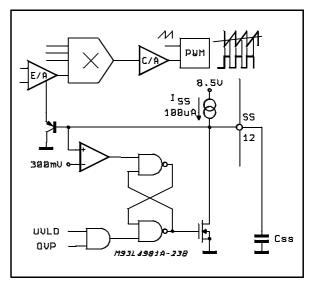
Figure 14.



**Pin 12.** SS (Soft start). This feature avoids current overload on the external Mosfet (Q) during the ramp-up of the output boosted voltage. An internal switch discharges the capacitor if output overvoltage or VCC undervoltage are detected. An internal current generator of  $100\mu$  with the external capacitor define the soft start time costant (see fig. 15). Because the voltage at the softstart pin acts on the E/A output (driving the multiplier with  $V_{VAOUT} = 5.1V$  typical voltage swing), the softstart time is defined by:

$$t_{SS} = C_{ss} \cdot \frac{V_{VA-OUT}}{I_{SS}}.$$

Figure 15.



This time (tss) depends on the application parameters (output voltage, input voltage, output capacitor value, boost inductor size, etc.) and normally the value amounts at some tens of msec.

**Pin 13.**  $V_{VA\text{-}OUT}$  (Error amplifier output). Output of the E/A that determinates the control of the boosted regulated voltage ( $V_O$ ). This pin has to be connected with a compensation network to the pin 14 (see fig.16).

Figure 16.

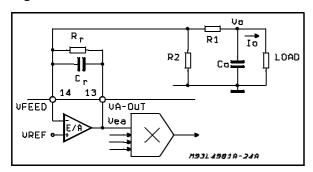
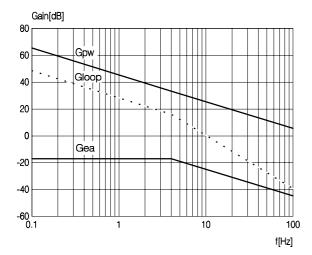


Figure 16a.



First of all, the system does not have to attempt to regulate the twice mains frequency output voltage ripple ( $\Delta V_0$ ) to avoid the line current distorsion. Moreover the system stability has to be ensured. The voltage open loop gain can be splitt in two separated blocks.

The first block small signal gain, is given by the ratio between the E/A output voltage (vea) and output voltage variation (vo) and is defined by the E/A network:

$$Gea' = \frac{vea}{vo} = \frac{1}{s \cdot R1 \cdot C_r}$$

Where Gea' is the E/A gain without  $R_r$  ref. fig. 16. R2 has no effect on the error amplifier gain be-

cause the inverting input potential is fixed to VREF. The Gea can be seen also as the ratio between the error amplifier output ripple and the imposed output voltage ripple ( $\Delta V_O$ ). The E/A output signal can swing between 1.28V to 5.1V. A value less than 2.5% of the effective E/A output swing voltage ( $V_{VAOUT}$ = 3.82V) could be chosen to fix the C<sub>r</sub>. So, the Gea defined at the output voltage ripple frequency, determinates the C<sub>r</sub> value to ensure the 100/120 Hz (2f) attenuation.

$$Gea \leq \frac{0.095V}{\Delta V_O}$$

$$C_r = \frac{1}{2 \cdot \pi \cdot 2f \cdot R1 \cdot Gea} \geq Ka \cdot \frac{\Delta V_O}{R1}$$

where: Ka = 1/60 for 50Hz and 1/72 for 60Hz mains frequency.

Lower  $C_r$  value could increase harmonic distortion. The second block (Power block) is represented by the output filter capacitor ( $C_O$ ) with its own reactance ( $X_{CO}$ ), the system has to be able to compensate the total external load variation through the E/A output response ( $\Delta Vea$ ). The power gain transfer function ( $G_{pw}$ ), for large variations can be written:

$$G_{pw} = I_O \frac{X_{CO}}{\Delta V_{ea}}$$

The total load variation (Io) to be considered is:  $P_{O(max)}/V_O$ :

$$G_{pw} = \frac{P_O \cdot X_{CO}}{V_O \cdot \Delta \, V_{ea}} \implies G_{pw} = \frac{P_O}{V_O \cdot \Delta V_{ea}} \cdot \frac{1}{s \cdot C_O}$$

The voltage open loop gain contains two poles in the origin, then stability problem can arise. Connecting the resistor ( $R_r$ ) in parallel to the capacitor  $C_r$  to shift the E/A pole from the origin to  $1/(Rr \cdot Cr)$ , the stability is ensured.

The crossover frequency  $f_c$  can be calculated by  $G_{pw} \cdot Gea^{\cdot} = 1$  and therefore:

$$f_{c} = \sqrt{\frac{P_{O}}{V_{O} \cdot \Delta \; \text{Vea} \cdot 2 \; \pi \cdot C_{O}}} \cdot \left(\frac{1}{2 \; \pi \cdot R_{1} \; C_{r}}\right)$$

To allow the highest DC gain maintaining a phase margin of at least  $22^{\circ}$ , the  $R_r$  maximum value is imposed as:

$$R_r \le \frac{2.75}{2 \; \pi \cdot f_c \cdot C_r}$$

The output filter capacitor value (C<sub>O</sub>) is related to the output voltage filtering (see Power section design).

**Pin 14.** VFEED (Error amplifier input). This pin (see fig. 16), connected to the boosted output voltage through a divider, allows the output D.C. voltage regulation. Neglecting the contribution of the E/A

feedback resistor ( $R_r$ ), the 5.1V reference and the output DC voltage ( $V_O$ ) define the ratio between R1 and R2:

$$\frac{R1}{R2} = \frac{V_0}{5.1V} - 1$$

To be considered that the R1, togheter with the feedback network(see pin 13 description) define the E/A gain. The R1/Rr ratio affects the load regulation (lower output current increases the output voltage) with the following relation:

$$\Delta V_{Omax} = \frac{\Delta V_{ea} \cdot R1}{R_r}$$

where: V<sub>Omax</sub> is the maximum output voltage variation due to the E/A gain reduction and load variation.

The R1 and R2 will be chosen in the high precision class:

**Pin 15.** P-UVLO (Programmable supply undervoltage threshold). An internal divider (between pin 19, pin 15 and ground) and an internal comparator with a threshold voltage of 1.28V fixes the default turn-on and turn-off 15.5V and 10V levels of the supply section (see fig. 17). Using an external divider ( $R_H$  and  $R_L$ ) it's possible to change the supply thresholds:  $R_H$  fixes the hysteresis,  $R_L$  fixes the turn-on threshold. To design a divider for a given supply threshold, is useful know (see fig. 17), the typical resistor value, useful to design the external divider, are:  $R_1 = 394k$ ,  $R_2 = 88k$  and  $R_3 = 58k$ . Anyway, in fig. 17a/b a diagram with threshold values and a table, useful for a fast choice of  $R_H$  and  $R_L$  are shown.

For DISABLE function see Appendix B.

**Pin 16.** SYNC (In/Out synchronization). Only for L4981A, this function allows the device to be synchronized with other circuits of a system (see

Figure 17: Programmable Under Voltage Lockout Thresholds

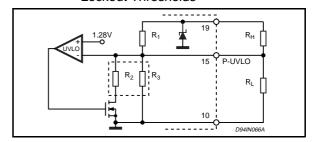


Figure 17a: V<sub>CCON</sub> and V<sub>CCOFF</sub> vs. R<sub>L</sub>

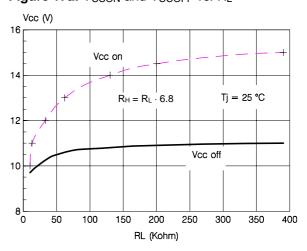


Figure 17b:

V <sub>CC ON</sub>	V <sub>CC OFF</sub>	RH	RL		
11V	10V	82kΩ	12kΩ		
12V	10.1V	220kΩ	$33$ k $\Omega$		
13V	10.5V	430kΩ	62kΩ		
14V	10.8V	909kΩ	133kΩ		
14.5V	10.9V	1.36MΩ	200kΩ		
15V	11V	2.7ΜΩ	390kΩ		

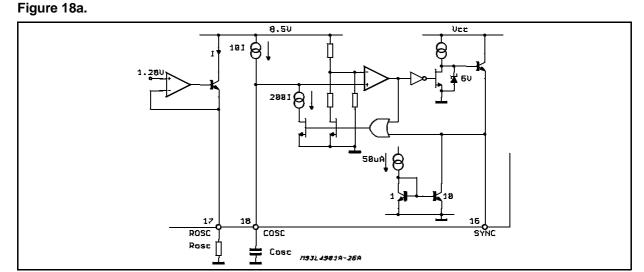
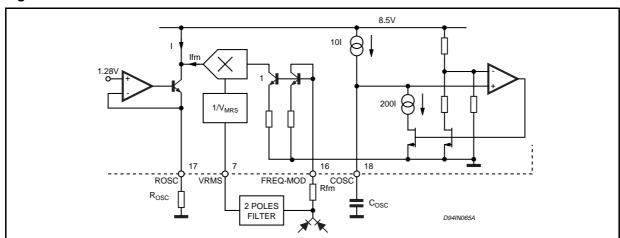


Figure 18b.



**Figure 18c:** Modulation Frequency Normalized in an Half Cycle of the Mains Voltage

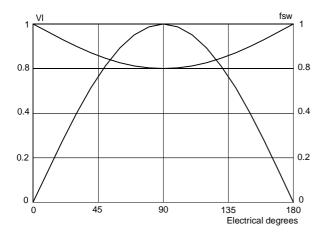


fig.18a). When the device is externally synchronized, the external clock has to satisfy these conditions: the signal amplitude must cross the threshold value (3.5V), the frequency has to be slightly higher than that programmed by the R-C constant (see pin 18) and the pulse width has to be at least 800 nsec.

If the device has to synchronize other circuits, the signal delivered by this pin is a positive pulse of 4.6V (0.5mA) and the pulse duration is equal to the sawtooth falltime.

The L4981B uses this pin to perform another function. If the application does not use the SYNC function, it is preferrable to focus the EMI filtering problem using the B version. Pin 16, named FREQ-MOD in B version, allows to change the switching frequency in order to spread the energy content over a wider spectrum range.

To perform the frequency modulation (see fig.18b), the pin must be connected, through a re-

sistor ( $R_{fm}$ ), to the rectified line voltage. This allows to change dinamically (cycle by cycle) the ( $C_{OSC}$ ) charge and the discharge currents that define the ramp slopes of the oscillator sawtooth. The effect of the resistor produces the frequency change (see fig.18c) between the nominal value ( $f_{sw}$ ) and its minimum value which occurs when the input voltage reaches the peak value ( $V_{lpk}$ ). The total frequency variation (see also pin 17 and 18) can be estimated by the formula:

$$\frac{\Delta f_{\text{SW}}}{f_{\text{SW}}} = K \frac{V_{IPK} \cdot R_{osc}}{V_{RMS} \cdot R_{fm}}$$

where:  $R_{fm}$  is the programming current resistor. K is a constant value = 0.1157 for R value in  $K\Omega$  and fsw in KHz.

A typical 20%  $\frac{\Delta \; f_{\text{SW}}}{f_{\text{SW}}}$  can be a good compromise.

**Pin 17.** ROSC (Oscillator resistor). An external resistor connected to ground, programs the charge and the discharge currents that pin 18 (Cosc) forces to the external capacitor. The reference voltage at pin 17 is 1.28V (see fig.18a/b)

To set the charge current, the relation is:

$$I_c \approx 10 \cdot \frac{1.28 V}{Rosc}$$

The discharge current is defined by:

$$I_d \approx 200 \cdot \frac{1.28 V}{R_{OSC}}$$

The maximum discharge current of  $I_d = 12mA$ , this means a minimum Rosc value of  $22K\Omega$ .

**Pin 18.** COSC (Oscillator capacitor). An external capacitor (see fig 18a/b), connected between this pin and ground, fixes the rise and fall time ( $t_r$  and  $t_f$ ) of the sawtooth oscillator according to the pre-

vious relations (pin 17) and therefore the switching frequency. The typical ramp valley-peak voltage (V<sub>srp</sub>) is fixed to 5V.

The period T is defined by:

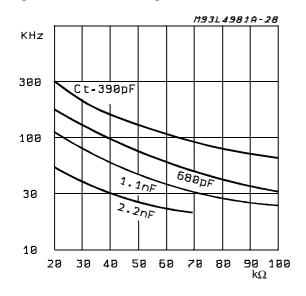
$$T = t_r + t_f = V_{Srp} \cdot C_{OSC} \left( \frac{1}{I_C} + \frac{1}{I_d} \right)$$

the switching frequency is:

$$f_{SW} = \frac{1}{T} \approx \frac{2.44}{R_{OSC} \cdot C_{OSC}}$$

See also Fig. 19

Figure 19: Oscillator Diagram



**Pin 19.** VCC (Supply voltage input). The very low current consumption feature before the turn-on threshold is reached. The undervoltage circuitry, with the threshold hysteresis of 5.5V typ. (see also pin 15) and an internal clamp at 25V (typ.) ensure the IC safety operation.

**Pin 20.** GDRV (Gate driver output). This output is internally clamped to 15V (see Fig. 20), to avoid ageing problems of the gate oxide. The output driver is normally connected to the gate of the power device through a resistor (say 5 to 50 Ohm) to avoid overshoot and to control the dl/dt of the switch.

#### **POWER SECTION DESIGN**

## **Booster Inductor**

The Boost Inductor design involves various parameters to be handled and there are different approaches to define them.

In continuous mode operation, the energy stored in the boost inductor in each switching cycle, is

Figure 20.

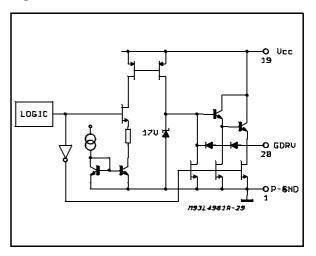
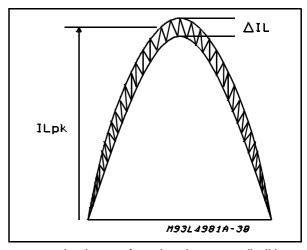


Figure 21.



not completely transferred to the output (bulk) capacitor. A quantity of energy is stored in the magnetic circuit, reducing in this way the input current ripple. This minimizes the line noise and reduces the input filter size (see fig.21).

The energy transferred from the boost inductor to the bulk capacitor in each cycle is:

$$E/cycle = \frac{1}{2} L \cdot (|I_{Lp}|^2 - |I_{Lv}|^2) = |L \cdot I_{Lt} \cdot \Delta I_L$$

where:

L = Boost Inductance

 $I_{Lp}$  = Inductor Peak Current ( $I_{Lt} + \Delta I_{L}/2$ )

 $I_{Lv}$  = Inductor Valley Current ( $I_{Lt}$  -  $\Delta I_{L}/2$ )

 $I_{Lt}$  = Instantaneous Line Current  $(I_{Lp} + I_{Lv})/2$ 

 $\Delta I_L$  = Twice Inductor Current Ripple ( $I_{Lp}$  -  $I_{LV}$ )

Because the instantaneous line current (I<sub>Lt</sub>) that corresponds to the average inductor current in the



cycle, draws a full rectified (half- sinusoidal) waveform, it is useful to refer to the AC line RMS and peak parameters:

$$I_{Lpk} = \sqrt{2} \cdot I_{Lrms}$$

where:  $I_{rms} = I_{Lrms} = P_I / V_{Irms}$  is the line current  $P_I = P_{O/\eta}$  is the input power  $\eta$  is the power yeld.

The power transferred by the inductor in each cycle

$$P_{t} = \frac{L \cdot I_{Lt} \cdot \Delta I_{L}}{t_{on}}$$

where:  $t_{on} = \delta / f_{sw}$  and  $\delta = (V_O - V_{lt}) / V_O$ 

For a given L, the twice ripple current  $\Delta I_L$  is the quantity associated to the transferred energy and can be calculated as a certain percentage of the  $I_{Lpk}$  inductor current.

$$\Delta I_L = \frac{V_{lt} \cdot (V_O - V_{lt})}{V_O \cdot f_{sw} \cdot L}$$

If the maximum V<sub>lpk</sub> value is higher than the V<sub>O</sub>/2,

the maximum  $\Delta I_L$  occours when  $V_{lt} = \frac{V_O}{2}$  and its

value is 
$$\Delta I_{L(max)} = \frac{V_O}{4 \cdot f_{SW} \cdot L}$$

If the  $V_{lpk}$  maximum value does not reach Vo/2 voltage value, the maximum  $\Delta I_L$  is reduced and its value is :

$$\Delta I_{L(max)} = \frac{V_{lpk} \; (V_O - V_{lpk})}{V_O \cdot f_{sw} \cdot L}$$

In continuous mode approch, the acceptable curent ripple level  $(K_r)$  can be considered between 10% to 35%.

$$K_r = \frac{\Delta I_L}{2 \cdot I_{Lpk}}$$

Smaller current ripple on the inductor involves smaller noise on the rectified main bus reducing the input filter size; but the ripple reduction will impose an increase of the boost inductor.

The high voltage, the flux density and the frequency range make the standard high frequency ferrite the most useful material in P.F.C. applications. To avoid the core saturation, related to the high permeability materials, it is necessary built an air-gap in order to allow an adequate magnetic force range (H+Hgap).

An easy approach, is to have an approximated minimum value of core size that could be used to perform the conversion:

Volume 
$$\geq K \cdot L \cdot I_{Lpk} \cdot \left(I_{Lpk} + \frac{\Delta I_L}{2}\right)$$

where : K = specific energy constant.

L = Boost inductor value in H.

The specific energy constant (K), mainly depends on the ratio between the gap length ( $I_{gap}$ ) and the effective length ( $I_{eff}$ ) of the magnetic core set and on the maximum  $\Delta B$  swing. Practically

$$K \approx 14 \cdot 10^{-3} \frac{I_{eff}}{I_{gap}}$$

can be used to get the minimum volume of the core set in cm<sup>3</sup>. After the minimum core-set size is estimated, the suitable type will be selected with technical and economic evaluations.

Next step will be the design of the coil parameters.

The above mentioned formula  $P_{Ot} = \frac{L \cdot I_{Lt} \cdot \Delta I_{L}}{t_{on}}$ 

if referred to the magnetic path, can be rewritten:

$$P_{Ot} = Ae \cdot I_{eff} \cdot H \cdot \frac{\Delta B}{t_{on}}$$

where: Ae = effective area of the core section. leff = effective magnetic path length.  $\Delta B$  = deviated magnetic flux density. H = magnetic field strength.

The ratio between the ferrite and the air path magnetic permeability, depends on the ferrite materials. Core materials for power application (such as B50/51), have a initial permeability value about 2500 times that of air. This means that, above a certain air-gap length percentage, it is possible to neglect the leff (length of the core) simplifing the calculation e.g. if a 1% of air-gap length, respect to the core length value is used, the error introduced is about 4%.

Rewriting 
$$(P_{Ot} = Ae \cdot I_{eff} \cdot H \cdot \frac{\Delta B}{t_{on}})$$

$$P_{Ot} \approx Ae \cdot I_{gap} \cdot H_{gap} \cdot \frac{\Delta B}{t_{on}}$$

equating to and simplifing  $P_{Ot} = \frac{L \cdot I_{Lt} \cdot \Delta I_{L}}{t_{on}}$ 

$$Ae \cdot I_{gap} \cdot H_{gap} \cdot \Delta B \approx L \cdot I_{Lt} \cdot \Delta I_{L}$$

Because:  $I_{gap} \cdot H_{gap} \approx N \cdot I_{Lt}$  and  $\Delta B = \mu_0 \cdot \Delta H$ 

$$Ae \cdot N \cdot \mu_0 \Delta H \approx I \cdot \Delta I_L$$

$$\Delta H \approx N \frac{\Delta I_L}{I_{Gap}}$$

and finally:

$$N \approx \sqrt{\frac{L \cdot I_{gap}}{\mu_0 \cdot Ae}}$$

This simplified relation is much easier to use than the complete one:

$$N \approx \sqrt{\frac{L}{\mu_o}} \left[ \frac{I_{gap}}{\sqrt{A_e} + \frac{\pi}{4} \cdot I_{gap}} + \frac{I_{eff}}{\mu_r \cdot Ae} \right]$$

After N has been defined, it's necessary to check the core for saturation of the magnetic path (rated N  $\cdot$  I<sub>max</sub> vs. Air-gap on ferrites databook). If the check is too close the rated limit, an increase of the Igap (gap lengh) and a new calculation will be necessary. Copper losses R<sub>L</sub>  $\cdot$  I $^2$ <sub>Lrms</sub> and former's winding space available will be considered for the wire selection.

An auxiliary winding can be used just to get a low cost supply for the I.C. It will be a low cost thin wire coil will be used and the number of turns is the only parameter to define.

#### **Input Bridge**

The input diodes bridge can be standard off-line, slow-recovery and low cost devices. The device selection considers just the input current (Irms) and the thermal data.

#### **Input Capacitor**

The input filter capacitor  $(C_{IN})$  has to sustain the input instantaneous voltage  $(V_{It})$ , with an imposed voltage ripple, during the turn-on  $(t_{on})$  time of the Mosfet.

The worst conditions will be found at the minimum rated input voltage V<sub>Irms(min)</sub>.

The maximum high frequency voltage ripple  $(r = \Delta V_1 / V_1)$  has to be imposed:

$$C_{IN} \ge K_r \frac{I_{rms}}{2 \cdot \pi \cdot f_{sw} \cdot r \cdot V_{Irms}}$$

Where:  $K_r$  is the current ripple coefficient. r = 0.02 to 0.08.

The  $C_{\text{IN}}$  maximum value is limited to avoid current distortion.

## **Output Bulk Capacitor**

The choice of the output bulk capacitor  $(C_O)$ , mainly depends on the electrical parameters that affect the filter performances and also on the subsequent application.

The D.C. output voltage and overvoltage, the output power and voltage ripple are the first parameters to consider in all applications. The RMS capacitor ripple current  $I_{C(2f)rms} = I_O/\sqrt{2}$  and so, the output voltage ripple ( $\Delta V_O$ ) will be:

$$\Delta V_0 = I_0 \sqrt{\frac{1}{(2 \pi \cdot 2f \cdot C_0)^2} + (ESR)^2}$$

With a low ESR capacitor can be simplify:

$$C_O = \frac{I_O}{2 \pi \cdot 2f \cdot \Delta V_O} = \frac{P_O}{2 \pi \cdot 2f \cdot \Delta V_O \cdot V_O}$$

Although the ESR, normally does not affect the output ripple parameter, it has to be considered in power losses account both for the rectified mains frequency and the switching frequency.

If the application (i.e. computer supply) has to guarantee a specified Hold-Up time ( $t_{\text{HOLD}}$ ), the capacitance sizeing criteria will change:

The C<sub>O</sub> has to deliver the supply energy for a certain time and a specific dropout voltage.

$$C_{O} = \frac{2 \cdot P_{O} t_{HOLD}}{V_{O \min}^{2} - V_{Op \min}^{2}}$$

where: V<sub>O\_min</sub> = minimum output voltage value (normally at the maximum load conditions)

V<sub>op\_min</sub> = minimum output operative voltage before the 'power fail' detection.

#### **Power Switch**

A power MOSFET is the active switch used in most application for its frequency features. It will be selected according with the output boosted voltage and the delivered power. There are two contributions for power losses in the mosfet: conduction losses and switching losses. The on-state power losses can be calculated using the formula:

$$P_{on-MOS} = I_{Qrms}^2 R_{dson}$$

One extimation of the switching losses can be done considering two separated quantities:

$$\begin{aligned} P_{\text{capacitive}} &\approx \left(\frac{10}{3} \cdot C_{\text{oss}} \cdot V_{\text{o}}^{1.5} + \frac{1}{2} C_{\text{ext}} \cdot V_{\text{o}}^{2}\right) \cdot f_{\text{sw}} \cdot \\ &P_{\text{crossover}} \approx V_{\text{O}} \cdot I_{\text{rms}} \cdot t_{\text{cr}} \cdot f_{\text{sw}} + P_{\text{rec}} \end{aligned}$$

where:  $C_{oss}$  is the Drain capacitance at  $V_{DS}$  = 25V.  $t_{cr}$  is the crossover time.

C<sub>ext</sub> is the external layout stray capacitance. P<sub>rec</sub> is the contribution due to the diode recovery.

To reduce the crossover losses a snubber network can be used.

#### **Booster diode**

The booster diode will be selected to withstand the output voltage and current. Moreover, it has to be as fast as possible in order to reduce the power switch losses.

The SGS-THOMSON Turboswitch™ diode series match this specifications, and are expecially suitable for this application.

The diode power losses can be split in two contri-

## **APPLICATION NOTE**

butions: conduction losses and switching losses. The conduction losses can be estimated by:

$$P_{Don} = V_{to} \cdot I_O + R_d \cdot I_{Drms}^2$$

where:  $V_{to}$  = threshold voltage  $R_d$  = differential resistance

#### Sense Resistor

The sense resistor produces the signal for the current feedback loop and for the overcurrent protection circuit.

An easy criterion to choose the sense resistance is to minimize the power dissipated assuring a sufficient signal to noise ratio.

#### A PRACTICAL EXAMPLE

The following PFC design example is referred to the evaluation board, realized for demostration purpose.

The design target specification are:

- a) UNIVERSAL AC input supply voltage V<sub>Irms</sub> = 88V to 264V
- b) DC output regulated voltage V<sub>O</sub> = 400V
- c) Rated output power Po = 200W
- d) Full load output ripple  $\Delta V_0 = \pm 8V$
- e) Maximum overvoltage value  $\Delta V_0 = 50V$
- f) Switching frequency f<sub>SW</sub> = 100kHz
- g) Maximum Inductor current ripple  $\Delta I_L = 35\%$  of  $I_{Lrms}$
- h) Worse condition efficiency (at minimum input voltage)  $\eta = 90\%$

To match the specifications the material selection, expecially for some critical components is an important step. The choice criterion for some of this components is here discribed.

#### **Power Mosfet:**

Since the Mosfet device has to sustain a mimimum blocking voltage value of 500V ( $V_{DSS}$   $V_{O}$  +  $\Delta V_{OUT}$ + $V_{marg}$ ), then the most important parameter for the selection is the  $R_{DSON}$  for its relation with the power dissipation.

The device STH/STW15NA50FI (or equivalent) with its 500V V<sub>DSS</sub> and the R<sub>DSON</sub> (R<sub>DSON</sub> = 0.4 $\Omega$  @ T = 25°C) of about 0.7 $\Omega$  at Tj = 100°C, is a good choice for the application. We can estimate its performance in this application.

-The maximum "on state" power dissipation evaluated at the minimum input mains voltage (see the above formulae) is:

 $\dot{P}_{on\text{-MOSmax}} = I_{Qrms}^2_{max} \cdot \dot{R}_{on} = 2.15 \cdot 0.7 \approx 3.3W.$ 

- The switching (on + off) losses can be estimated as:

$$P_{crossover} \approx t_{cr} \cdot V_O \cdot f_{sw} \cdot I_{rms}$$

To take into account the booster diode recovery effect, an easy approach is to compute two times the current value (at turn-on), this means 1.5 times the above value:

$$P_{crossover} \approx 1.5 \cdot 30 \text{ns} \cdot 400 \text{V} \cdot 100 \text{kHz} \cdot 2.15 \text{A} = 3.9 \text{W}$$

The capacitive losses at turn-on to be added are:

$$P_{capacitive} \approx \left(\frac{10}{3} \cdot C_{oss} \cdot V_o^{1.5} + \frac{1}{2} C_{ext} \cdot V_o^2\right) \cdot f_{sw} = 3W.$$

To reduce the switching losses a voltage snubber (RCD) has been used.

#### **Booster Diode:**

Because of the continuous inductor current mode, the Mosfet has to recover the booster diode minority-carrier at turn on. This makes advantageous the choice of an ultra fast recovery time diode. The SGS-THOMSON Turboswitch<sup>TM</sup> family offers the best solution for this kind of application. The STTA506D has been selected to match the board parameters. Considering the frequency of the application and the fast performance of the diode, its power dissipation is mainly due to the conduction losses:

$$P_D = V_{TO} \cdot I_o + R_d \cdot I_{drms}^2 = 1.15V \times 0.5A + 0.07\Omega \times 1.28A^2 = 0.7W$$

Where: V<sub>TO</sub> and R<sub>d</sub> are the diode parameters.

#### **Booster Inductor:**

The inductor design starts defining the minimum L value to limit the high frequency ripple current  $\Delta I_L$  (for the given frequency), under the rated value. It results a minimum inductance of 0.7mH (0.75mH has been imposed). Using a gapped ferrite the minimum volume needed is about 6.7cm $^3$ . So the core set B1ET3411A (7.5cm $^3$ ) has been selected; its effective magnetic path lenght = 79mm define a gap of 1.4mm placed in the central leg to reduce the magnetic radiation, while its effective core area = 97mm $^2$  and considering a  $\Delta B$  up to 250mT, defines the number of the primary winding = 75 turns.

To minimize the copper losses (skin and proximity effect), a multiwire solution with a bunch of 20 wires of 32 AWG (0.2mm) has been used. The maximum resistive copper losses can be calculated with the formula:

$$\begin{split} \text{P}_{\text{CU}} &= \text{I}_{\text{Lrms}}^2 \cdot \text{R}_{\text{CUdc}} + \text{I}_{\text{Lhfrms}}^2 \cdot \text{R}_{\text{CUhf}} = 1.4\text{W} \\ \text{where: } \text{R}_{\text{CUdc}} &= 170\text{m}\Omega \text{ (at } 100^{\circ}\text{C)}, \\ \text{R}_{\text{CUhf}} &= 5.1\Omega \text{ (at } 100\text{kHz)}, \\ \text{I}_{\text{Lrms}} &= 2.5\text{A}, \\ \text{I}_{\text{Lhfrms}} &= 2.5\text{A} \cdot 0.35 \, / \, \sqrt{12} \, = 0.25\text{A} \end{split}$$

# **Output Filter Capacitor:**

For the output capacitor ( $C_O$ ), in this application, the output voltage ripple is the parameter considered. A  $100\mu F/450V$  has been chosen obtaining a full load ripple voltage of  $\pm 8V$ .

## **Input Filter Capacitor:**

To smooth the high frequency ripple, a capacitor of 220nF across the rectified mains (bridge output) has been used. This capacitor allows the demoboard works well. In normal application an EMI filter is interposed between the mains and the PFC circuit. The EMI filter design is not described in this paper, anyhow it is used in the following evaluation.

#### **Sense Resistor:**

The parallel of three metal film resistors (0.22 $\Omega$ ), has been used to obtain the resistance of

Figure 22: 200W Evaluation Board Circuit.

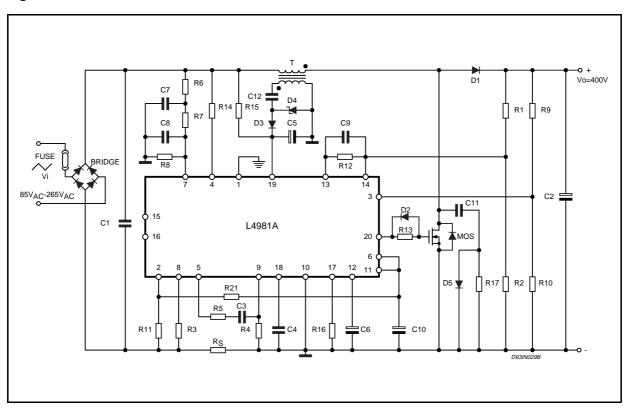
 $R_S$ = 73m $\Omega$  that gives a good signal level, with a maximum power dissipation:

$$P_{Rs} = R_S(I_{Lrms}^2 + I_{Lhfrms}^2) = 0.46W$$

## **Supply Circuit:**

To have a stand alone working demoboard, an IC supply circuitry has been added. This circuitry has been designed for a fast start-up and low power consumption. The start-up is realized with Q2, Q3, Dz, R15, R19, R20 and is turned-off by the VREF signal after the turn-on threshold has been reached. At running the supply, delivered by an auxiliary winding on the booster inductor, is optimized to work with large load variation; anyway if the output power (Po) goes under 10W this circuit doesn't work well and instabilty can happen. To work at so low power a different supply solution has to be used.

The other components has been designed with the criteria already described in this paper and their values are reported in the schematic.



T= primary: 75 turns of litz wire 20 x 32 AWG (0.2mm) secondary: 8 turns of # 32AWG (0.20mm)

core: B1ET3411A THOMSON - CSF

gap: 1.4mm for a total primary inductance of 0.7mH

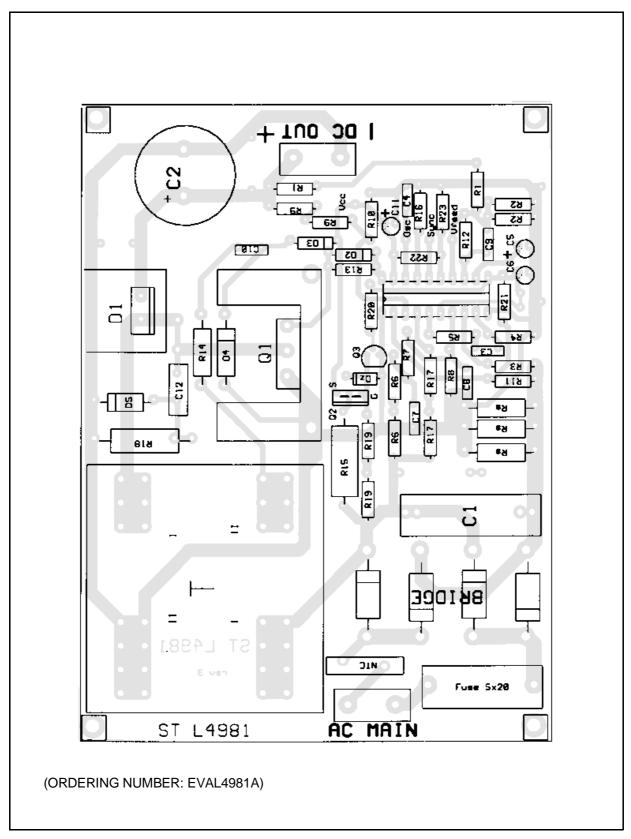
 $f_{sw} = 100kHz$ 

 $V_O = 400V$ ;  $P_O = 200W$ 

Ref. also OREGA P.N. 473201 A9



Figure 23: P.C. Board and Component Layout of Evaluation Board Circuit (1:1 scale)



## **EVALUATION RESULTS**

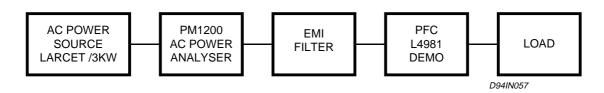
The evaluation board has been designed using a fast not dissipative start-up circuit (Q2, Q3, R19, R20) even if a simple one could be used and a Turn-off snubber to reduce the MOS power dissipation. The fig. 24 and fig. 25 show the Turn-on and the Turn-off MOS waveform.

Further there is a possibility to change the input threshold voltage using an external divider (R23 and R22) and if an inrush current problem arises a NTC resistor could be used.

The PFC demoboard performance has been evaluated testing the following parameters:

PF (power factor), A-THD (percentage of current total harmonic distortion), H3..H9 (percentage of current's  $n^{th}$  harmonic amplitude),  $\Delta V_{0}$  (output voltage ripple),  $V_{0}$  (output voltage),  $\eta$  (efficiency).

The test configuration, equipment and results are shown below:



Vi	f	Pi	PF	A-THD	Н3	Н5	H7	Н9	<b>V</b> O	$\Delta oldsymbol{V}_{O}$	РО	η
(V <sub>rms</sub> )	(Hz)	(W)		(%)	(%)	(%)	(%)	(%)	(V)	(V)	(W)	(%)
88	60	222	0.999	2.94	1.98	0.61	0.55	0.70	390	8	200	90.2
110	60	220	0.999	1.79	1.40	0.40	0.31	0.28	392	8	201	91.6
132	60	218	0.999	1.71	1.16	0.40	0.35	0.31	394	8	202	92.8
180	50	217	0.999	1.88	1.52	0.65	0.40	0.34	396	8	203	93.8
220	50	217	0.997	2.25	1.68	0.83	0.57	0.48	398	8	204	94.2
260	50	216	0.995	3.30	1.84	1.30	0.39	0.73	400	8	205	95.2

Figure 24: Turn-on Switch.

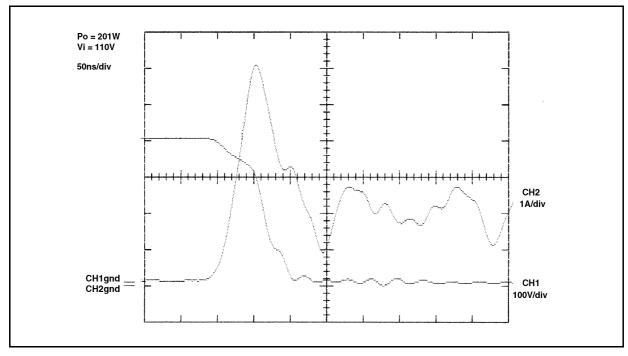
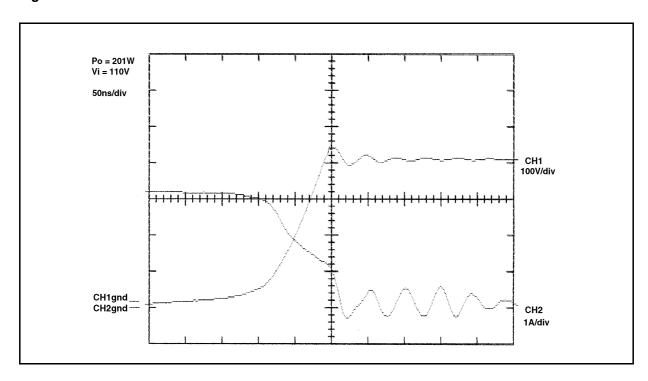


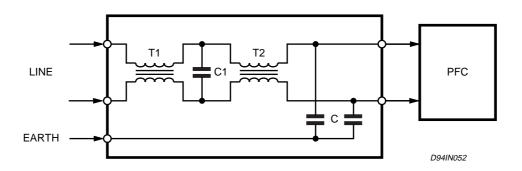
Figure 25: Turn-off Switch.



## **EMI/RFI FILTER**

The harmonic content measurement has been done using an EMI/RFI filter interposed between

the AC source and the demoboard under test, while the efficiency has been calculated without the filter contribution.



Where:

 $\begin{array}{ll} T1 = 1 mH & C1 = 0.33 \mu F, \, 630 V \\ T2 = 27 mH & C2 = 2.2 nF, \, 630 V \end{array}$ 

#### **APPENDIX A**

## LFF (pin 6) Function.

Since in Power Factor applications the Error Amp. compensation network has to filter the mains frequency contents, in order to reduce harmonic distortions, the crossover frequency of the loop gain must be low. This involves a poor load transient response.

An additional function (LFF) is available in L4981A/B devices. It is expecially suitable to modify the multiplier output current, proportionally to the load, in order to improve the system response bypassing the E/A.

The control is working with VLFF voltage between 1.7V and 5.1V.

In fig. A1 is shown an application example to explain this function. An external OP-AMP has been used to get the suitable signal voltage avoiding sense resistor (R1) power dissipation.

In the real application the sense resistor is often replaced by sense transformer.

## Design criteria:

It is avisable to ensure a minimum VLFF  $\cong$  2V at the minimum output current.

Since the OP-AMP (LM258) Vol = 0.7V (@ 1mA), to get the minimum voltage at VLFF, 1.3V has to be added. A resistor devider tied to the reference voltage (pin 11 of the controller) shifts the output of the OP-AMP.

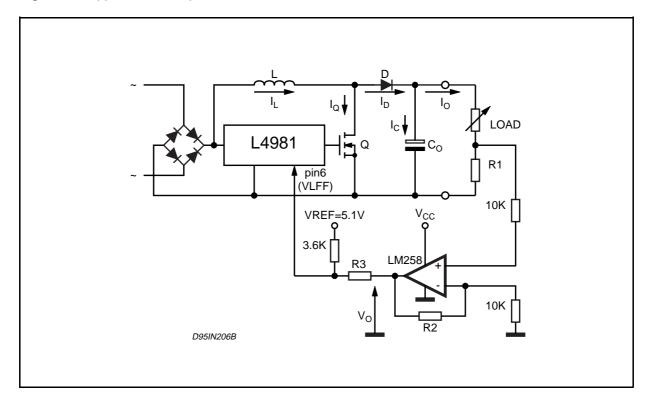
therefore 1.3V = 
$$\frac{(5.1V - 0.7V)}{R3 + 3.6k \Omega} \cdot R3 \implies R3 = 1.3k \Omega$$

The OP-AMP supply voltage is the same used for PFC controller ( $V_{CC}$ ) and its gain if fixed in order to produce  $V_O = 5.1V$  at the maximum load ( $I_{O max}$ ).

$$V_O = R1 \cdot I_{Omax} \cdot \left(1 + \frac{R2}{10k}\right) = 5.1V$$

E.g. for  $I_{Omax}$  = 3A. R1 = 0.1 $\Omega$  - 1W R2 is roughly 160K  $\Omega$ .

Figure A1: Application example.



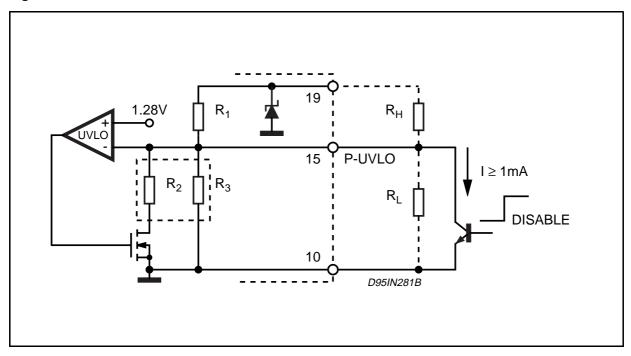
#### **APPENDIX B**

#### **Disable**

Sometimes it is useful to disable the controller. For example, in a complete system in which a PWM regulator follows the PFC stage, at low output power it is advantageous to shutdown the PFC section to improve the overall system efficiency (stand-by / sleep mode). Likewise most of controllers, one way to do this (using L4981A/B), is pulling down either the Soft-Start or the E/A output pin . In addition the L4981A/B can be disabled grounding the P-UVLO (pin 15) see fig B1.

The P-UVLO function has been designed to program the supply thresholds by means of an external divider (see application note for details) but it can be effectively used for this purpose forcing a voltage below the internal reference (1.28V). Besides turning off the driver output stage this method puts the controller in "before start-up" condition and gives the advantage of minimizing the supply consumption of the IC.

Figure B1.



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